

### November 2013

# FDB2710 N-Channel PowerTrench<sup>®</sup> MOSFET 250 V, 50 A, 42.5 mΩ

### Features

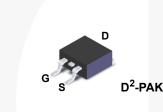
- $R_{DS(on)}$  = 36.3 m $\Omega$  (Typ.)@  $V_{GS}$  = 10 V, I<sub>D</sub> = 25 A
- High Performance Trench Technology for Extremely Low  $R_{\text{DS}(\text{on})}$
- Low Gate Charge
- High Power and Current Handing Capability

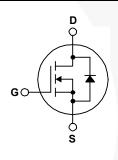
## **General Description**

This N-Channel MOSFET is produced using Fairchild Semiconductor's PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

### Applications

- Synchronous Rectification
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies





### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted

Symbol	Parameter		FDB2710	Unit	
V <sub>DS</sub>	Drain-Source Voltage		250	V	
V <sub>GS</sub>	Gate-Source voltage			± 30	V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C	)	50 31.3	A A
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	See Figure 9	A
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2		(Note 2)	145	mJ
dv/dt	Peak Diode Recovery dv/dt (Note		(Note 3)	4.5	V/ns
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate above 25°C		260 2.1	W W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
Τ <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

### **Thermal Characteristics**

Symbol	Parameter	FDB2710	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.48	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (1 in <sup>2</sup> pad of 2 oz copper), Max.	40	°C/W

	-		•					-	
FDB2710 FDB2710		FDB2710	D <sup>2</sup> -PAK 330 mm			24 mm		800 units	
Electric	al Cha	racteristics T	s = 25°C unless otherwise	e noted					
Symbol	Cal Characteristics T <sub>C</sub> = 25°C ur Parameter			Conditions		Min	Тур	Max	Unit
Off Charac	teristics								
			ge $V_{GS} = 0V$ ,	I <sub>D</sub> = 250μΑ, T <sub>J</sub> = 25°C		250			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdow Coefficier	vn Voltage Temperatu ht	ro	$I_D = 250 \mu A$ , Referenced to 25°C			0.25		V/°C
I <sub>DSS</sub>	Zero Gate	e Voltage Drain Curre		V, V <sub>GS</sub> = 0V V, V <sub>GS</sub> = 0V,T <sub>C</sub> = 125°	с			1 500	μΑ μΑ
I <sub>GSSF</sub>	Gate-Bod	y Leakage Current, F						100	nA
I <sub>GSSR</sub>	Gate-Bod	y Leakage Current, R	everse V <sub>GS</sub> = -30	V, V <sub>DS</sub> = 0V				-100	nA
On Charac	teristics								1
V <sub>GS(th)</sub>	Gate Threshold Voltage		$V_{DS} = V_{GS}$	, I <sub>D</sub> = 250μA		3.0	4.0	5.0	V
R <sub>DS(on)</sub>	Static Dra	in-Source On-Resista	ance V <sub>GS</sub> = 10V	, I <sub>D</sub> = 25A			36.3	42.5	mΩ
9 <sub>FS</sub>	Forward <sup>-</sup>	Fransconductance	V <sub>DS</sub> = 10V	, I <sub>D</sub> = 25A			63		S
Dynamic C	haracteris	tics							•
C <sub>iss</sub>	Input Cap	acitance					5470	7280	pF
C <sub>oss</sub>	Output Ca	apacitance		V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	426	570	pF	
C <sub>rss</sub>	Reverse	Transfer Capacitance	1 = 1.000112			97	146	pF	
Switching	Character	istics							
t <sub>d(on)</sub>	Turn-On Delay Time			V <sub>DD</sub> = 125V, I <sub>D</sub> = 50A		80	170	ns	
t <sub>r</sub>	Turn-On I	Rise Time	V <sub>GS</sub> = 10V	V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 25Ω			252	515	ns
t <sub>d(off)</sub>	Turn-Off I	Delay Time					112	235	ns
t <sub>f</sub>	Turn-Off I	Fall Time			(Note 4)		154	320	ns
Qg	Total Gate	e Charge		$V_{DS} = 125V, I_D = 50A$ $V_{GS} = 10V$ (Note 4)			78	101	nC
Q <sub>gs</sub>	Gate-Sou	rce Charge	V <sub>GS</sub> = 10V				34	,	nC
Q <sub>gd</sub>	Gate-Dra	in Charge					18		nC
Drain-Sour	ce Diode	Characteristics and	Maximum Ratings				1	1	1
I <sub>S</sub>	Maximum	Continuous Drain-So	ource Diode Forward	Current				50	Α
I <sub>SM</sub>	Maximum	Pulsed Drain-Source	Diode Forward Curre	prward Current				150	А
V <sub>SD</sub>	Drain-Sou	urce Diode Forward V	oltage V <sub>GS</sub> = 0V,	I <sub>S</sub> = 50A				1.2	V
t <sub>rr</sub>	Reverse	Recovery Time	V <sub>GS</sub> = 0V,	I <sub>S</sub> = 50A			163		ns
Q <sub>rr</sub>	Reverse	Recovery Charge	dI <sub>F</sub> /dt =100	)A/μs			1.3		μC

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

Package Marking and Ordering Information

Package

**Reel Size** 

Tape Width

Quantity

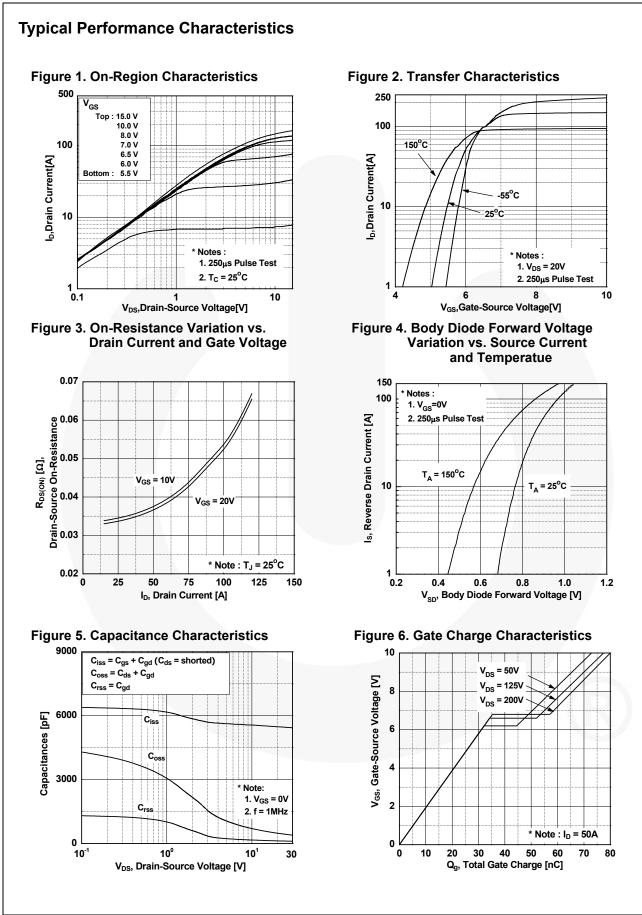
Device

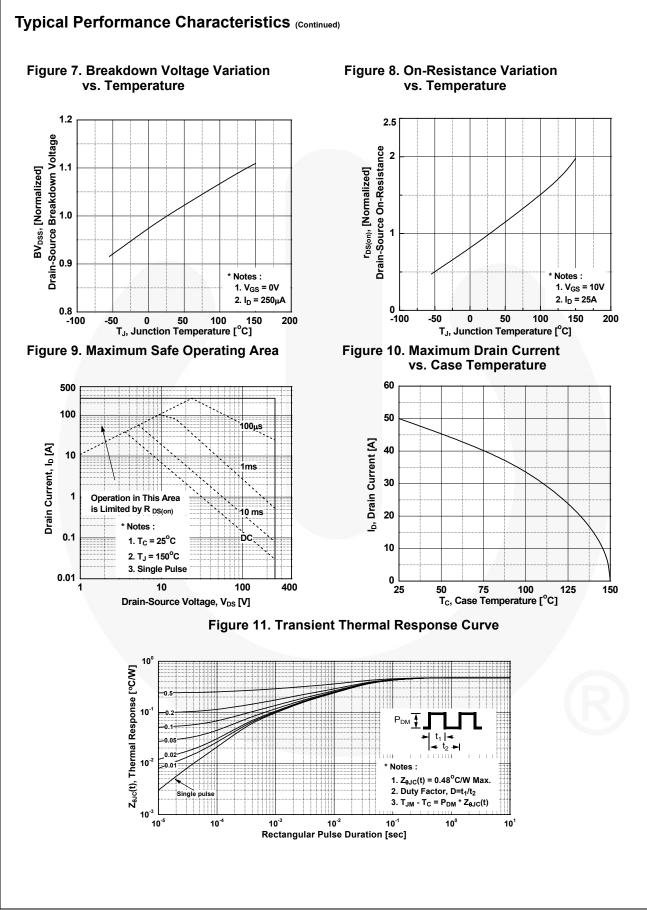
**Device Marking** 

2. L = 1mH, I<sub>AS</sub> = 17A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , Starting T<sub>J</sub> = 25°C

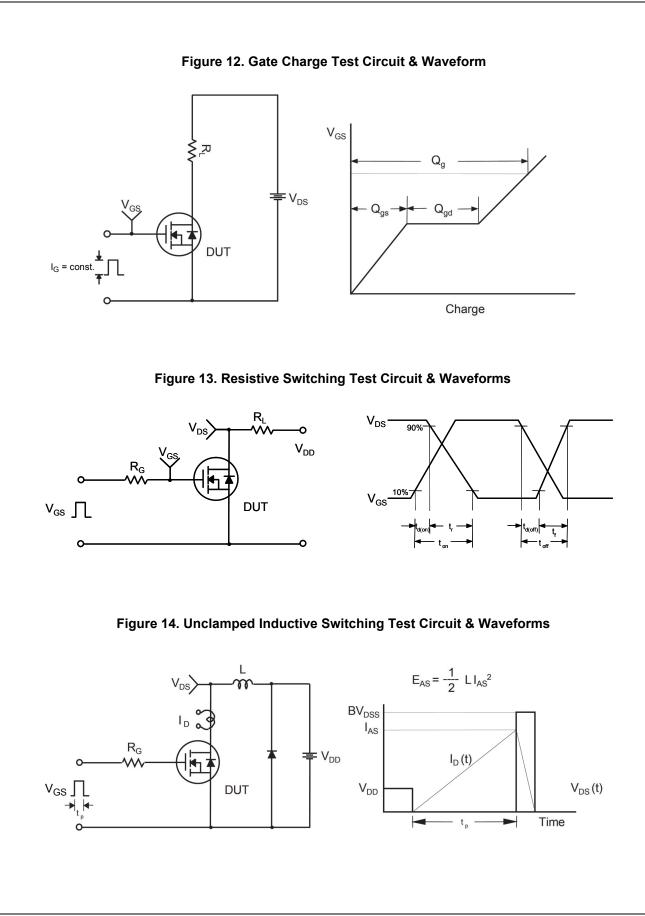
3. I\_{SD} \leq 50A, di/dt  $\leq$  100A/µs, V\_{DD}  $\leq$  BV\_{DSS}, Starting T\_J = 25°C

4. Essentially Independent of Operating Temperature Typical Characteristics





4



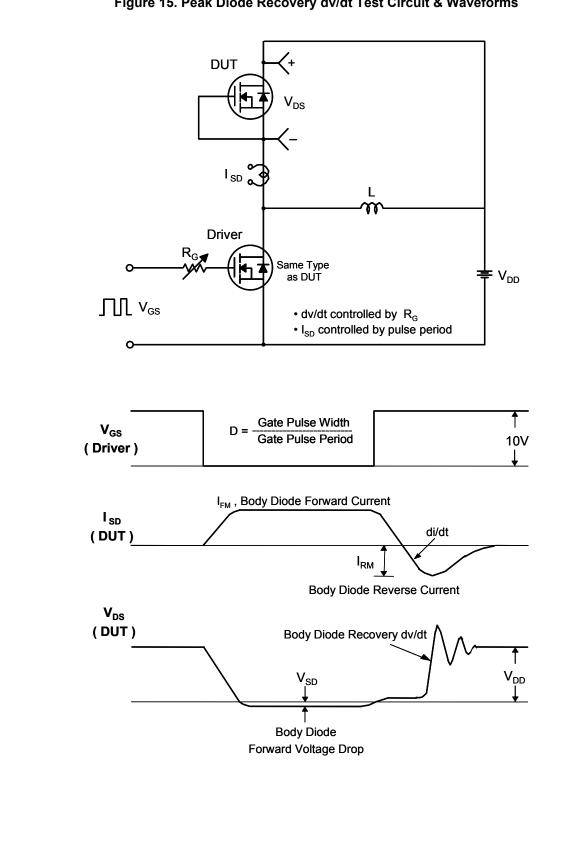
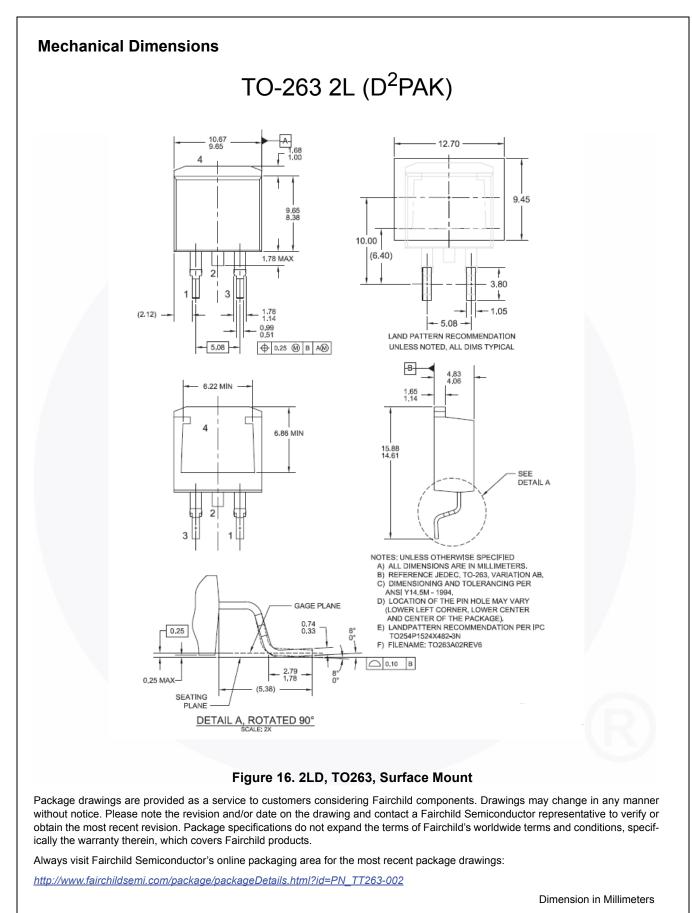


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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